

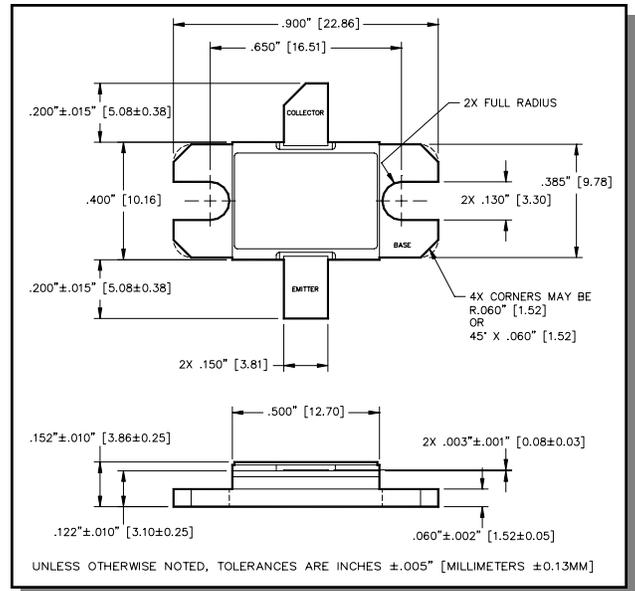
Radar Pulsed Power Transistor
100W, 1.1-1.3 GHz, 3μs Pulse, 30% Duty

M/A-COM Products
Released, 30 May 07

Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

Outline Drawing



Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	70	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	I_C	9.0	A
Power Dissipation @ +25°C	P_{TOT}	350	W
Storage Temperature	T_{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Electrical Specifications: $T_C = 25 \pm 5^\circ\text{C}$ (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	$I_C = 50\text{mA}$		BV_{CES}	70	-	V
Collector-Emitter Leakage Current	$V_{CE} = 32\text{V}$		I_{CES}	-	10	mA
Thermal Resistance	$V_{CC} = 32\text{V}$, $P_{out} = 100\text{W}$	$F = 1.1, 1.2, 1.3\text{ GHz}$	$R_{TH(JC)}$	-	0.5	°C/W
Input Power	$V_{CC} = 32\text{V}$, $P_{out} = 100\text{W}$	$F = 1.1, 1.2, 1.3\text{ GHz}$	P_{IN}	-	16	W
Power Gain	$V_{CC} = 32\text{V}$, $P_{out} = 100\text{W}$	$F = 1.1, 1.2, 1.3\text{ GHz}$	G_P	8.0	-	dB
Collector Efficiency	$V_{CC} = 32\text{V}$, $P_{out} = 100\text{W}$	$F = 1.1, 1.2, 1.3\text{ GHz}$	η_C	52	-	%
Input Return Loss	$V_{CC} = 32\text{V}$, $P_{out} = 100\text{W}$	$F = 1.1, 1.2, 1.3\text{ GHz}$	RL	-	-9	dB
Load Mismatch Tolerance	$V_{CC} = 32\text{V}$, $P_{out} = 100\text{W}$	$F = 1.1, 1.2, 1.3\text{ GHz}$	VSWR-T	-	3:1	-
Load Mismatch Stability	$V_{CC} = 32\text{V}$, $P_{out} = 100\text{W}$	$F = 1.1, 1.2, 1.3\text{ GHz}$	VSWR-S	-	1.5:1	-

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ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

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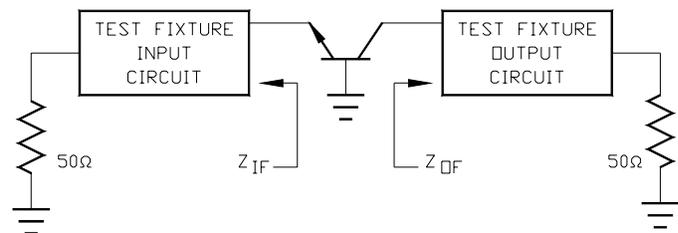
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Typical RF Performance

Freq. (GHz)	Pin (W)	Pout (W)	Gain (dB)	Ic (A)	Eff (%)	RL (dB)	VSWR-S (1.5:1)	VSWR-T (3:1)
1.1	14.9	100	8.26	5.23	59.8	-12.4	S	P
1.2	12.8	100	8.92	4.79	65.3	-12.1	S	P
1.3	13.7	100	8.63	4.98	62.7	-10.8	S	P

RF Test Fixture Impedance

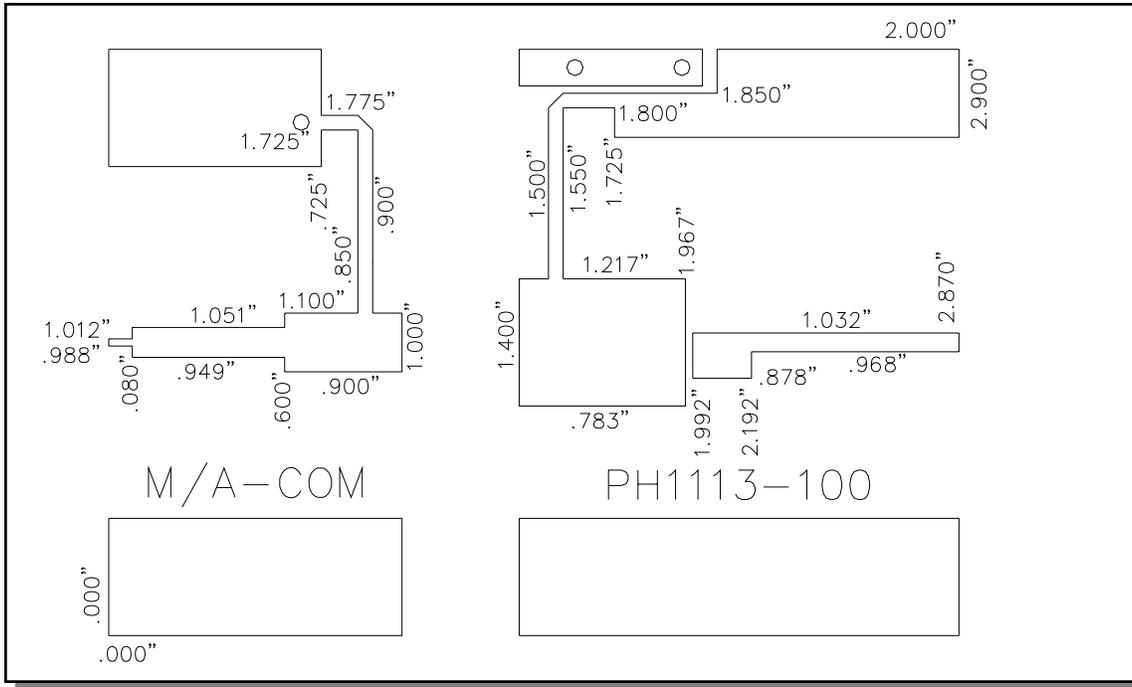
F (GHz)	Z _{IF} (Ω)	Z _{OF} (Ω)
1.1	5.8 - j3.4	3.0 - j1.7
1.2	5.6 - j1.8	3.0 - j1.5
1.3	5.9 - j0.4	2.8 - j1.3



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Test Fixture Circuit Dimensions



Test Fixture Assembly

